

MOSFETs Silicon N-Channel MOS (U-MOS<sup>™</sup> VII)

# TPCC8076

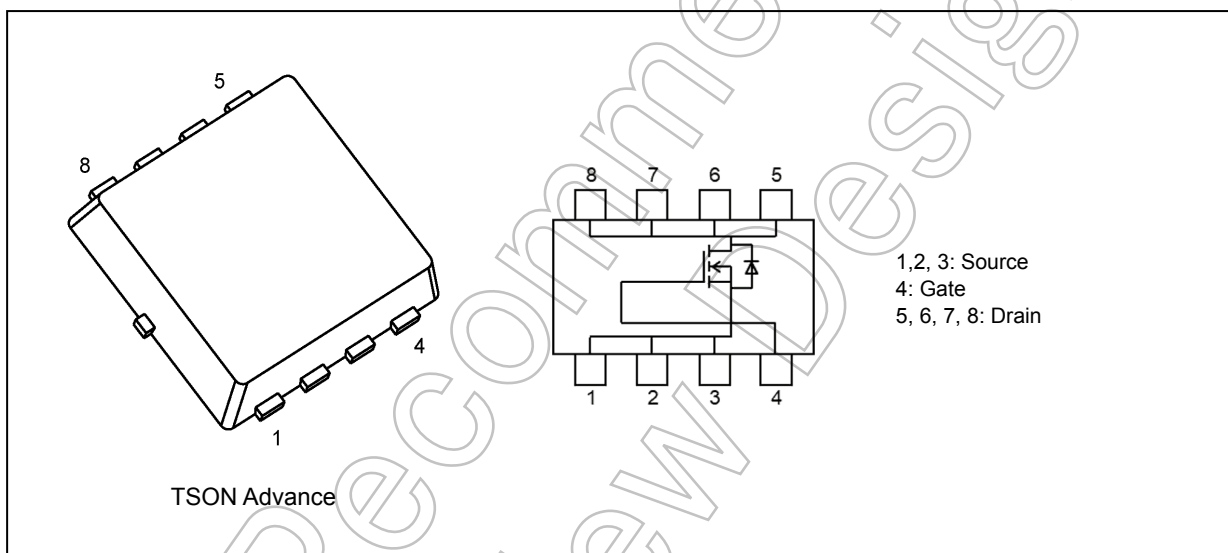
## 1. Applications

- Lithium-Ion Secondary Batteries
- Notebook PCs
- Mobile Equipments

## 2. Features

- (1) Small footprint due to a small and thin package
- (2) Low drain-source on-resistance:  $R_{DS(ON)} = 3.7 \text{ m}\Omega$  (typ.) ( $V_{GS} = 10 \text{ V}$ )
- (3) Low leakage current:  $I_{DSS} = 10 \text{ }\mu\text{A}$  (max) ( $V_{DS} = 33 \text{ V}$ )
- (4) Enhancement mode:  $V_{th} = 1.3 \text{ to } 2.3 \text{ V}$  ( $V_{DS} = 10 \text{ V}$ ,  $I_D = 0.3 \text{ mA}$ )

## 3. Packaging and Internal Circuit



Start of commercial production

2010-06

## 4. Absolute Maximum Ratings (Note) ( $T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	$V_{\text{DSS}}$	33	V
Gate-source voltage	$V_{\text{GSS}}$	$\pm 20$	
Drain current (DC) (Note 1)	$I_{\text{D}}$	27	A
Drain current (pulsed) (Note 1)	$I_{\text{DP}}$	81	
Power dissipation ( $T_c = 25^\circ\text{C}$ )	$P_{\text{D}}$	39	W
Power dissipation ( $t = 10\text{ s}$ ) (Note 2)	$P_{\text{D}}$	1.9	
Power dissipation ( $t = 10\text{ s}$ ) (Note 3)	$P_{\text{D}}$	0.7	W
Single-pulse avalanche energy (Note 4)	$E_{\text{AS}}$	82	mJ
Avalanche current	$I_{\text{AR}}$	27	A
Channel temperature	$T_{\text{ch}}$	150	$^\circ\text{C}$
Storage temperature	$T_{\text{stg}}$	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods"), and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

## 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance ( $T_c = 25^\circ\text{C}$ )	$R_{\text{th(ch-c)}}$	3.2	$^\circ\text{C/W}$
Channel-to-ambient thermal resistance ( $t = 10\text{ s}$ ) (Note 2)	$R_{\text{th(ch-a)}}$	65.7	$^\circ\text{C/W}$
Channel-to-ambient thermal resistance ( $t = 10\text{ s}$ ) (Note 3)	$R_{\text{th(ch-a)}}$	178	$^\circ\text{C/W}$

Note 1: Ensure that the channel temperature does not exceed  $150^\circ\text{C}$ .

Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 4:  $V_{\text{DD}} = 24\text{ V}$ ,  $T_{\text{ch}} = 25^\circ\text{C}$  (initial),  $L = 0.1\text{ mH}$ ,  $R_{\text{G}} = 1\ \Omega$ ,  $I_{\text{AR}} = 27\text{ A}$

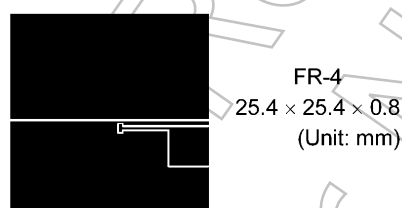


Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

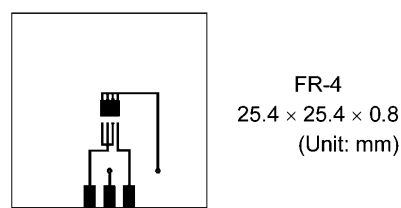


Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

## 6. Electrical Characteristics

### 6.1. Static Characteristics ( $T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	$I_{GSS}$	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$	—	—	$\pm 10$	$\mu\text{A}$
Drain cut-off current	$I_{DSS}$	$V_{DS} = 33\text{ V}, V_{GS} = 0\text{ V}$	—	—	10	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	33	—	—	V
	$V_{(BR)DSX}$	$I_D = 10\text{ mA}, V_{GS} = -20\text{ V}$	18	—	—	
Gate threshold voltage	$V_{th}$	$V_{DS} = 10\text{ V}, I_D = 0.3\text{ mA}$	1.3	—	2.3	
Drain-source on-resistance	$R_{DS(ON)}$	$V_{GS} = 4.5\text{ V}, I_D = 13.5\text{ A}$	—	4.9	6.2	$\text{m}\Omega$
		$V_{GS} = 10\text{ V}, I_D = 13.5\text{ A}$	—	3.7	4.6	

### 6.2. Dynamic Characteristics ( $T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	$C_{iss}$	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	2500	—	$\text{pF}$
Reverse transfer capacitance	$C_{rss}$		—	120	—	
Output capacitance	$C_{oss}$		—	430	—	
Switching time (rise time)	$t_r$	See Figure 6.2.1.	—	2.9	—	$\text{ns}$
Switching time (turn-on time)	$t_{on}$		—	10	—	
Switching time (fall time)	$t_f$		—	9.5	—	
Switching time (turn-off time)	$t_{off}$		—	48	—	

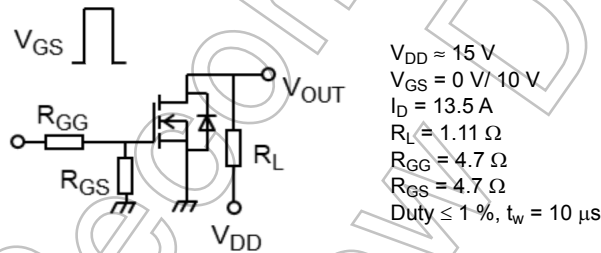


Fig. 6.2.1 Switching Time (Fig.)

### 6.3. Gate Charge Characteristics ( $T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Total gate charge (gate-source plus gate-drain)	$Q_g$	$V_{DD} \approx 24\text{ V}, V_{GS} = 10\text{ V}, I_D = 27\text{ A}$	—	34	—	$\text{nC}$
Gate-source charge 1	$Q_{gs1}$		—	7.4	—	
Gate-drain charge	$Q_{gd}$		—	4	—	

### 6.4. Source-Drain Characteristics ( $T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse drain current (pulsed) (Note 5)	$I_{DRP}$	—	—	—	81	A
Diode forward voltage	$V_{DSF}$	$I_{DR} = 27\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.2	V

Note 5: Ensure that the channel temperature does not exceed  $150^\circ\text{C}$ .

## 7. Marking

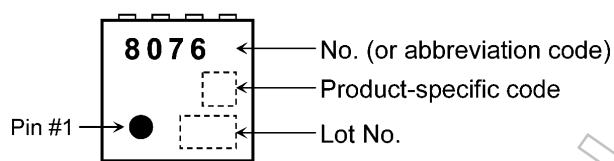


Fig. 7.1 Marking

Not Recommended  
for New Design

## 8. Characteristics Curves (Note)

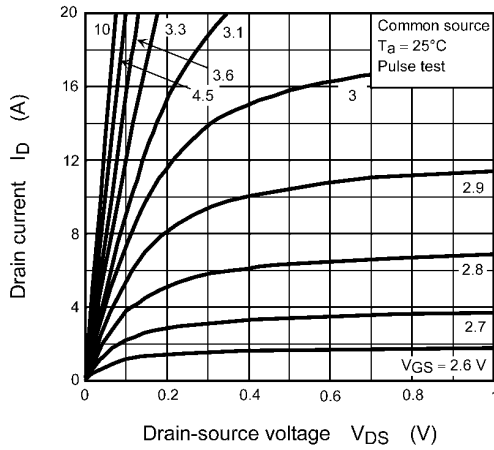


Fig. 8.1  $I_D - V_{DS}$

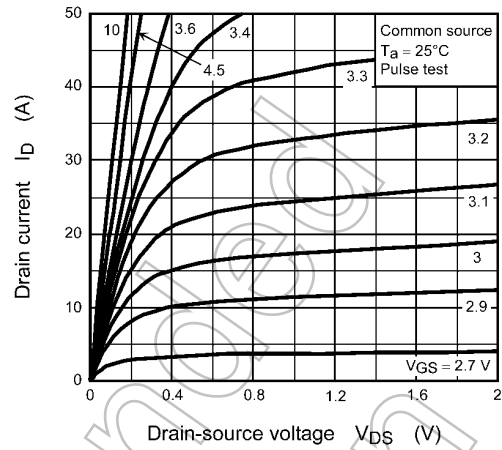


Fig. 8.2  $I_D - V_{DS}$

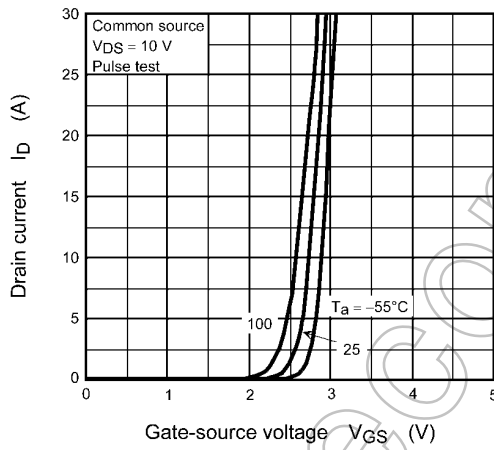


Fig. 8.3  $I_D - V_{GS}$

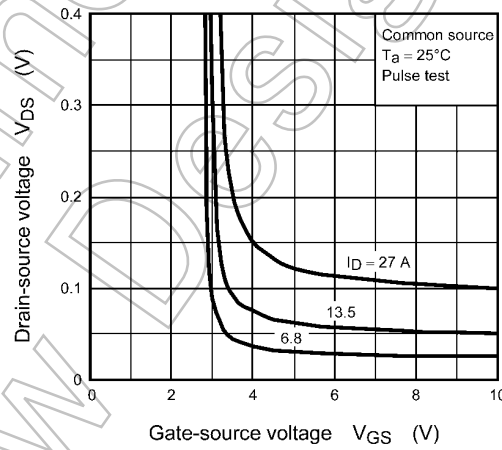


Fig. 8.4  $V_{DS} - V_{GS}$

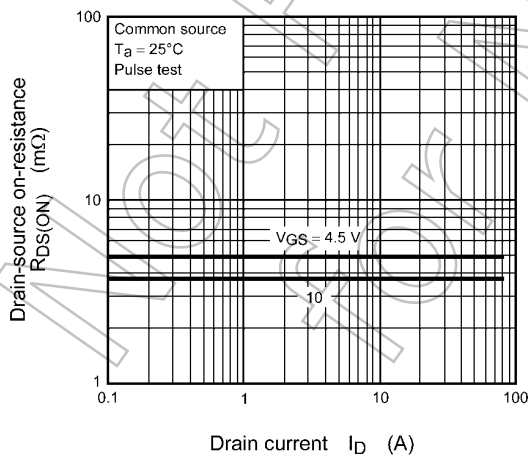


Fig. 8.5  $R_{DS(ON)} - I_D$

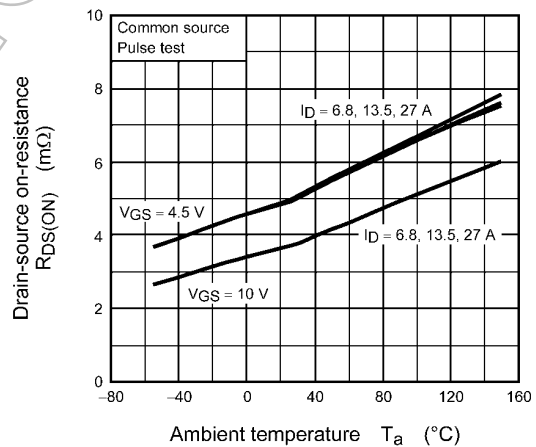


Fig. 8.6  $R_{DS(ON)} - T_a$

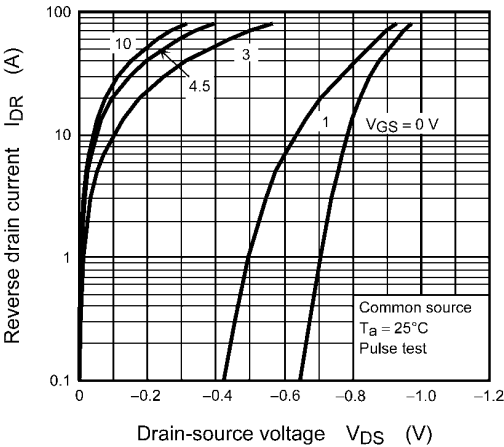


Fig. 8.7  $I_{DR} - V_{DS}$

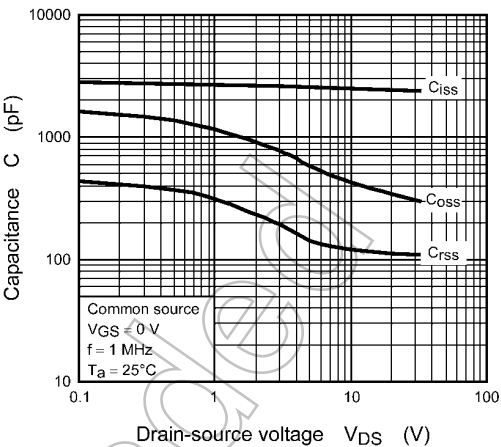


Fig. 8.8 Capacitance -  $V_{DS}$

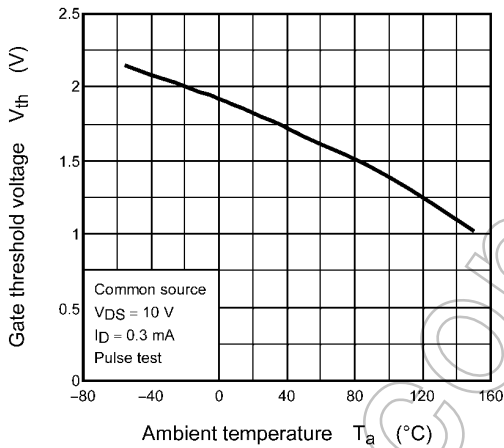


Fig. 8.9  $V_{th} - T_a$

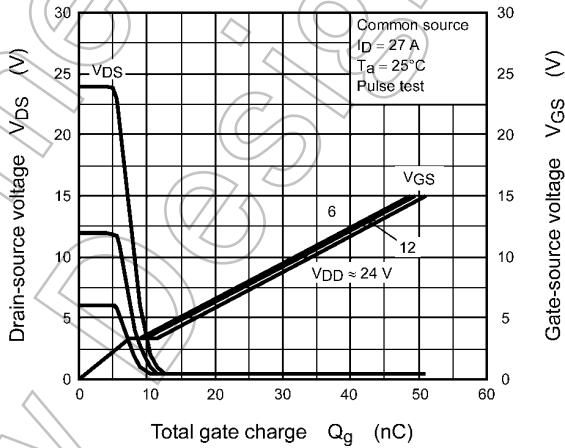


Fig. 8.10 Dynamic Input/Output Characteristics

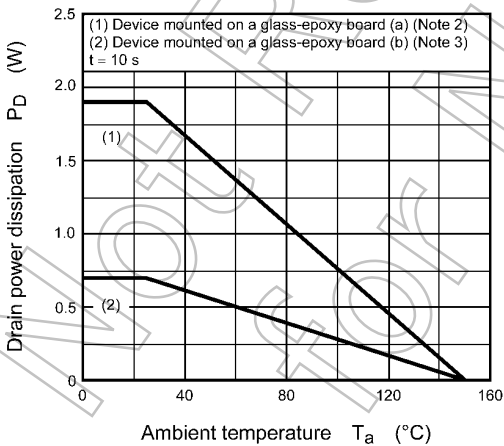


Fig. 8.11  $P_D - T_a$   
(Guaranteed Maximum)

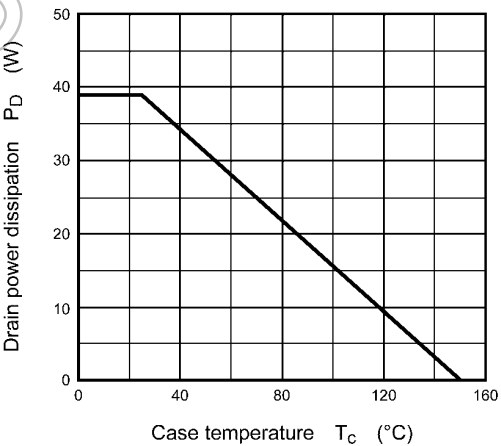


Fig. 8.12  $P_D - T_c$   
(Guaranteed Maximum)

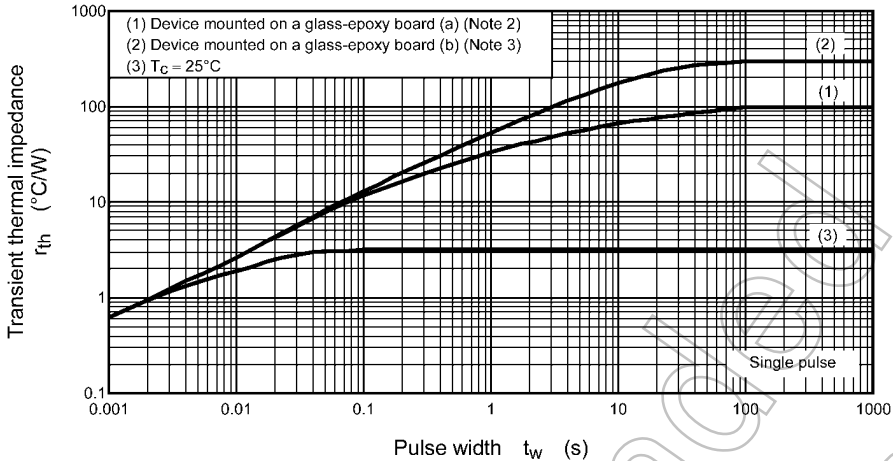


Fig. 8.13  $r_{th} - t_w$   
(Guaranteed Maximum)

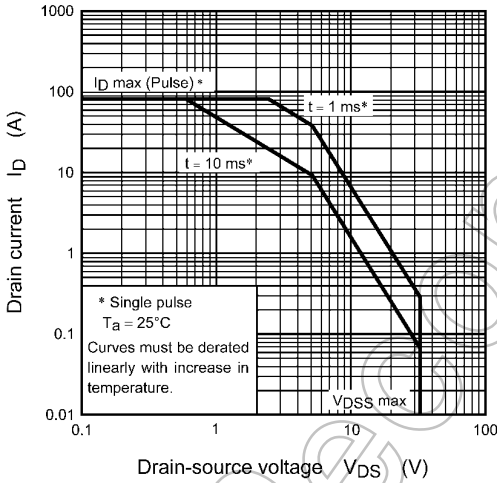
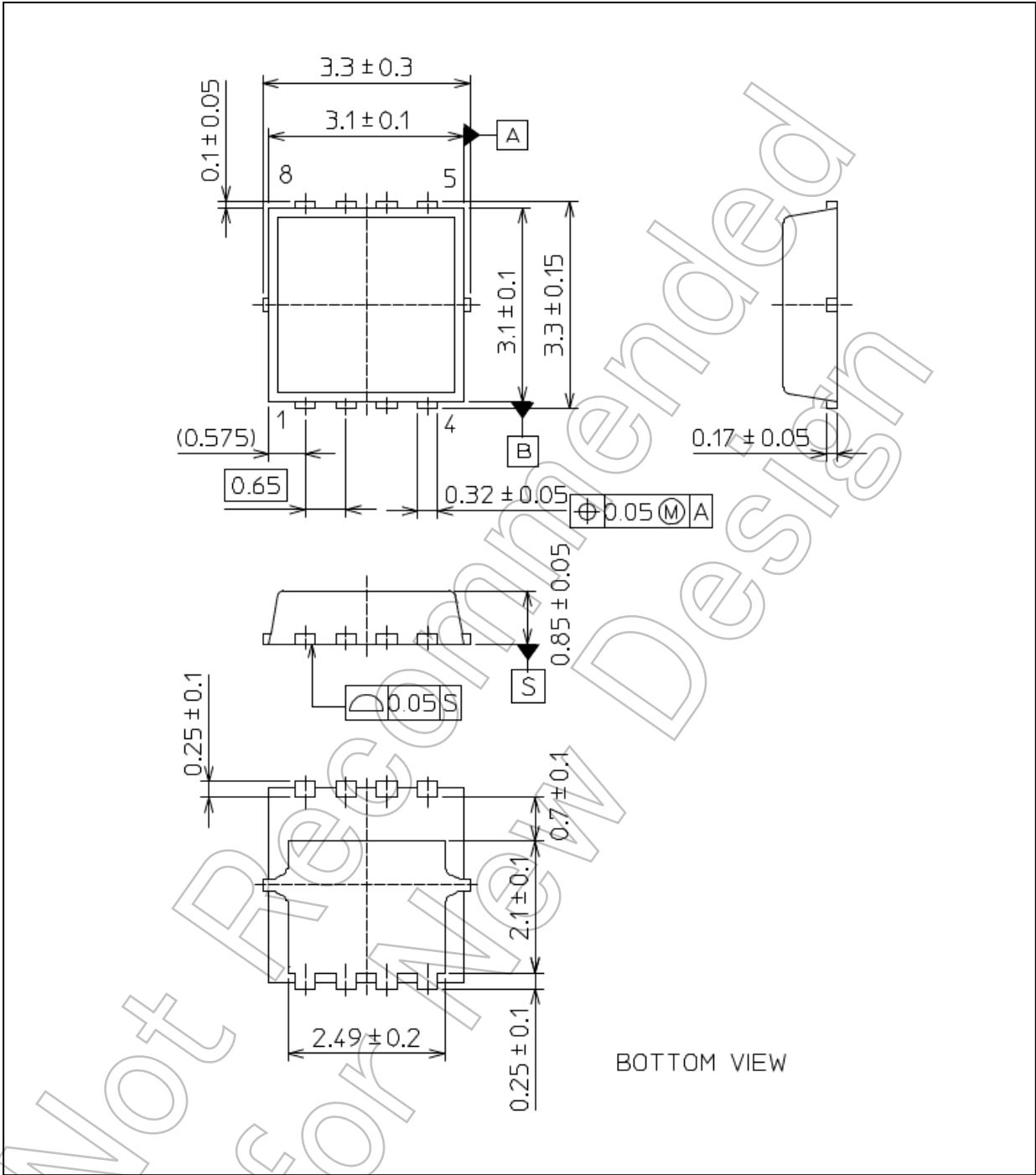


Fig. 8.14 Safe Operating Area  
(Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Package Dimensions

Unit: mm



Weight: 0.02 g (typ.)

Package Name(s)
TOSHIBA: 2-3X1S
Nickname: TSON Advance



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